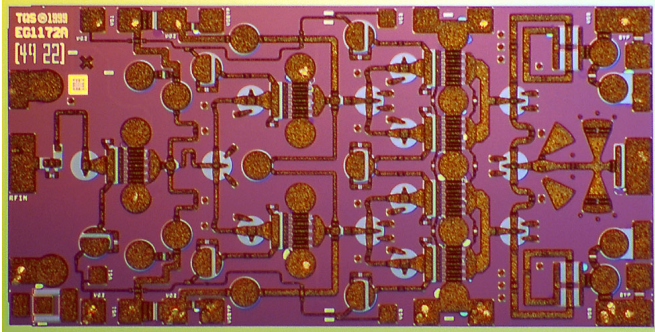


27 - 32 GHz 1W Power Amplifier

TGA1172



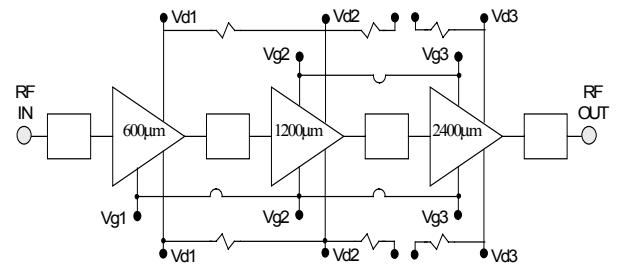
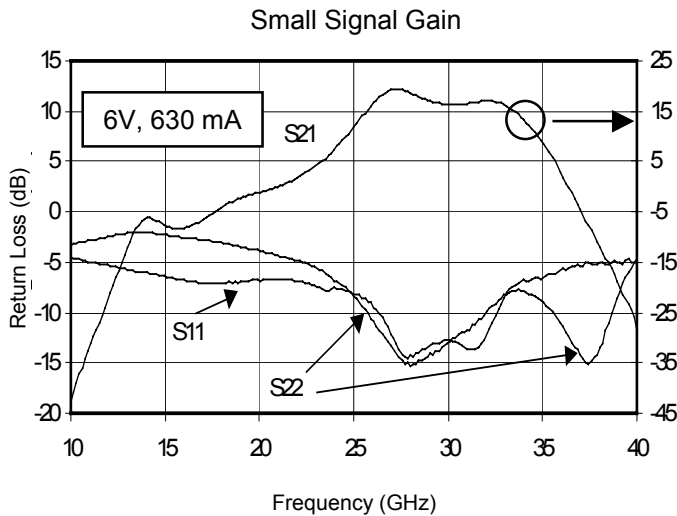
Chip Dimensions 2.69 mm x 1.37 mm

Key Features

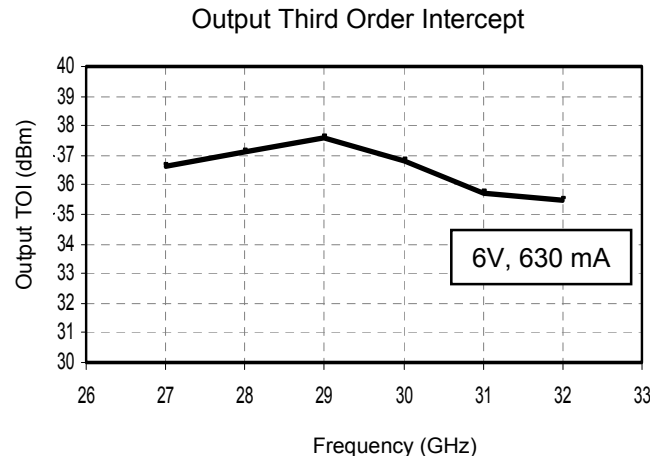
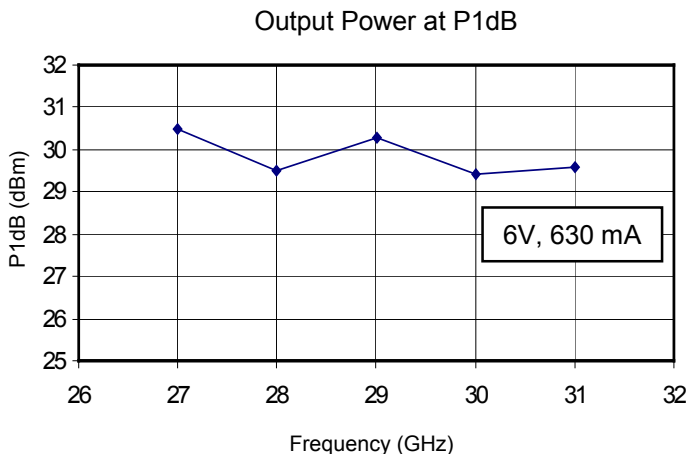
- 0.25 um pHEMT Technology
- 18 dB Gain at 28 GHz
- 29 dBm Nominal P1dB
- 37dBm OTOI typical at 28GHz
- Input/Output RL < -10 dB
- Bias 6 - 7V @ 630 mA

Primary Applications

- Point-to-Point Radio
- Point-to-Multipoint Communications
- Ka Band Sat-Com



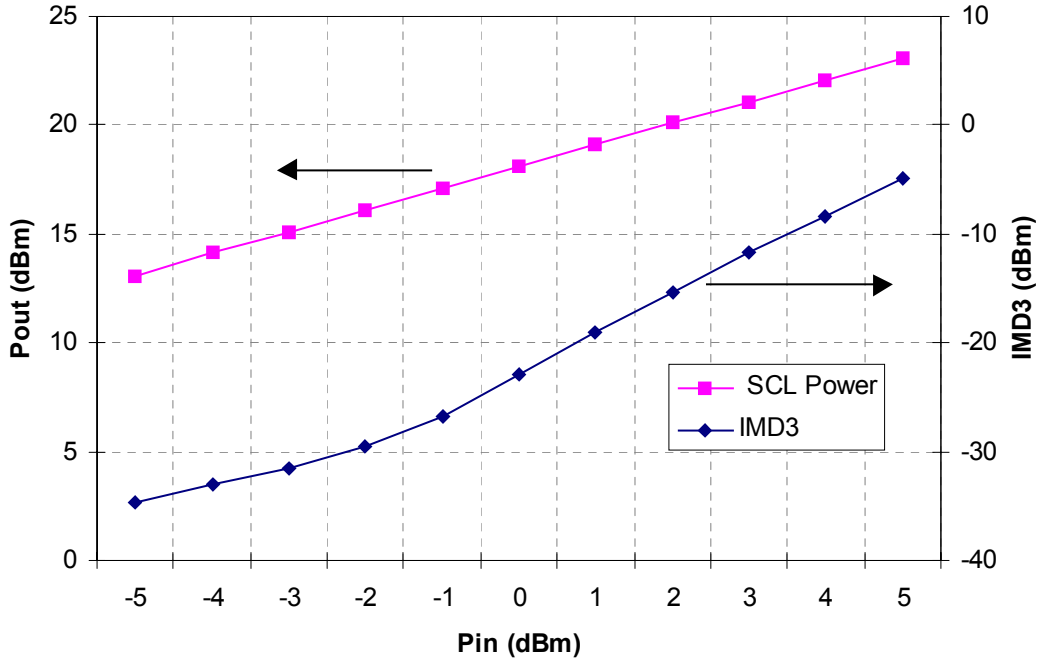
Amplifier Topology



Note: Devices designated as EPU are typically early in their characterization process prior to finalizing all electrical and process specifications. Specifications are subject to change without notice

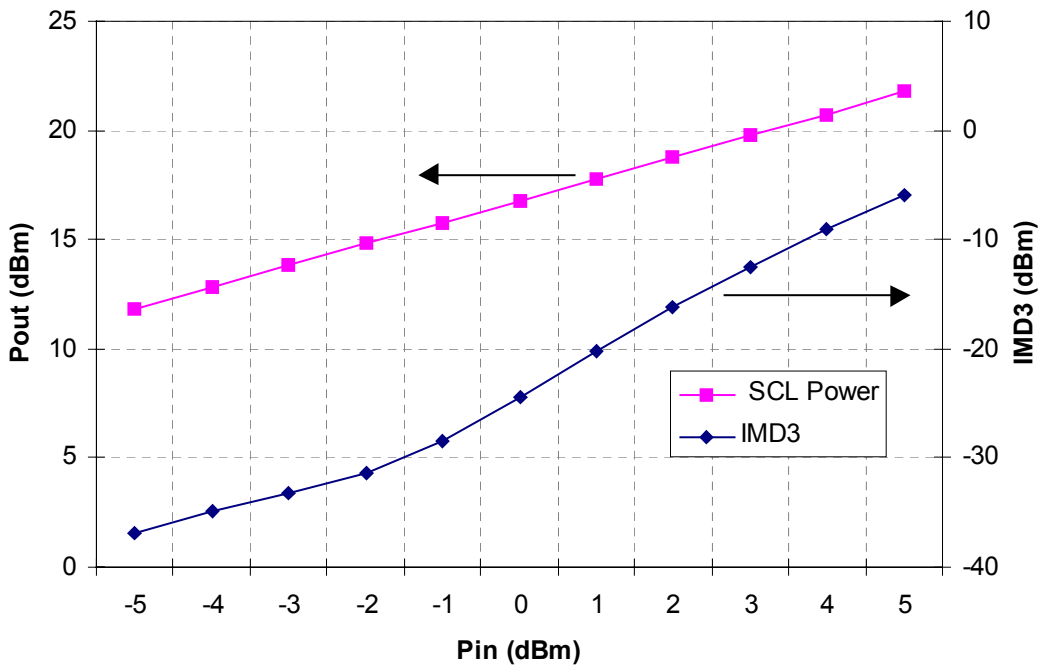
TGA1172 Single tone pout and IMD3 vs Pin

Frequency = 28GHz, 6V, 630 mA

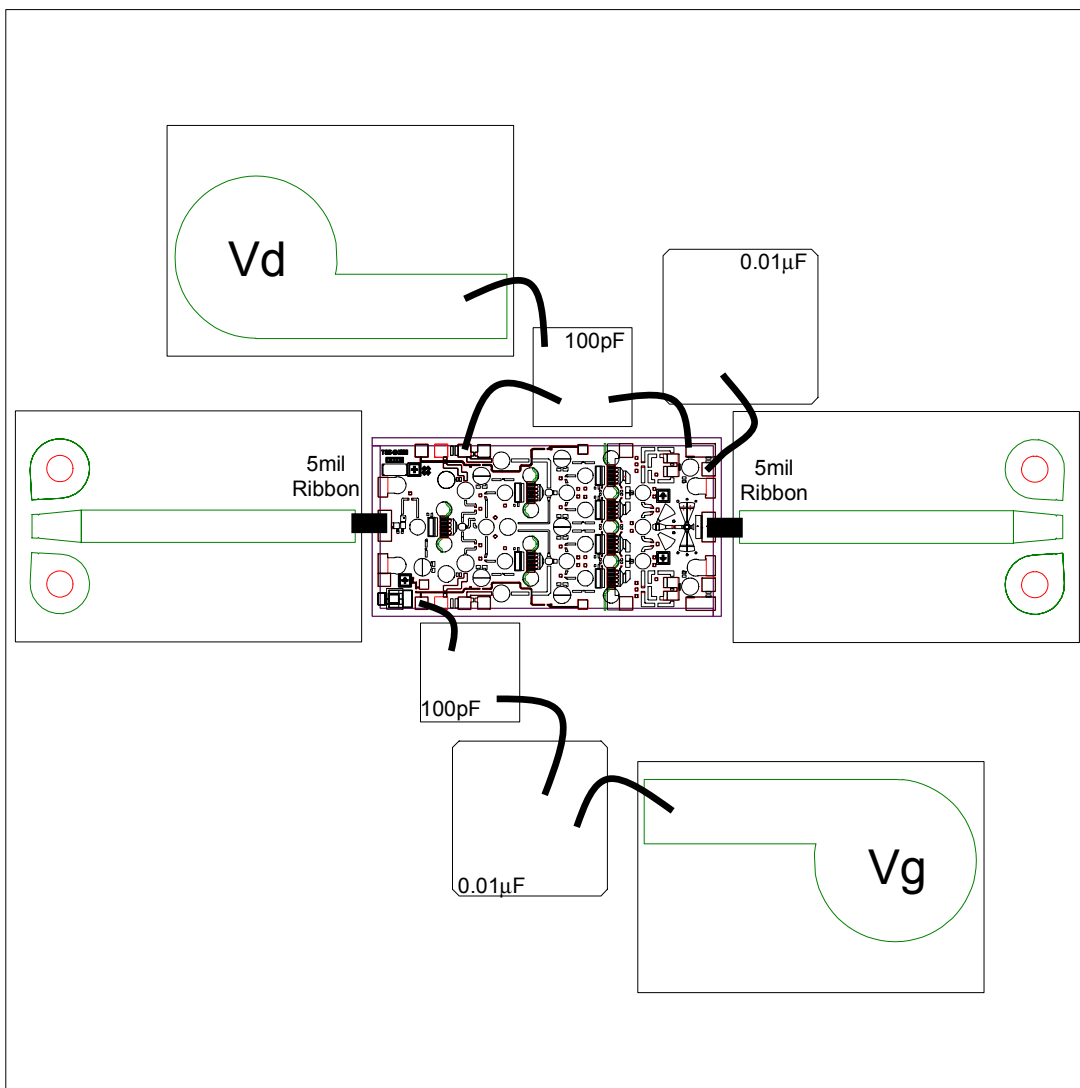


TGA1172 Single tone pout and IMD3 vs Pin

Frequency = 31GHz, 6V, 630 mA



Note: Devices designated as EPU are typically early in their characterization process prior to finalizing all electrical and process specifications. Specifications are subject to change without notice.



Chip Assembly and Bonding Diagram

GaAs MMIC devices are susceptible to damage from Electrostatic Discharge. Proper precautions should be observed during handling, assembly and test.

Note: Devices designated as EPU are typically early in their characterization process prior to finalizing all electrical and process specifications. Specifications are subject to change without notice.

Assembly Process Notes

Reflow process assembly notes:

- AuSn (80/20) solder with limited exposure to temperatures at or above 300°C
- alloy station or conveyor furnace with reducing atmosphere
- no fluxes should be utilized
- coefficient of thermal expansion matching is critical for long-term reliability
- storage in dry nitrogen atmosphere

Component placement and adhesive attachment assembly notes:

- vacuum pencils and/or vacuum collets preferred method of pick up
- avoidance of air bridges during placement
- force impact critical during auto placement
- organic attachment can be used in low-power applications
- curing should be done in a convection oven; proper exhaust is a safety concern
- microwave or radiant curing should not be used because of differential heating
- coefficient of thermal expansion matching is critical

Interconnect process assembly notes:

- thermosonic ball bonding is the preferred interconnect technique
- force, time, and ultrasonics are critical parameters
- aluminum wire should not be used
- discrete FET devices with small pad sizes should be bonded with 0.0007-inch wire
- maximum stage temperature: 200°C

GaAs MMIC devices are susceptible to damage from Electrostatic Discharge. Proper precautions should be observed during handling, assembly and test.

Note: Devices designated as EPU are typically early in their characterization process prior to finalizing all electrical and process specifications. Specifications are subject to change without notice.